

### AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method for forming a pattern, comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed, each of the unit panels including a plurality of gate lines and data lines defining a plurality of pixels, a thin film transistor in each pixel, and a pixel electrode in each pixel;

providing a cliché on which a plurality of grooves are formed, the cliché being divided into a plurality of portions corresponding to the unit panels of the substrate; filling resist in the grooves;

transferring the resist in the grooves of one divided portion of the cliché on a whole area of a blanket applied on a surface of a printing roll by contacting and rotating the printing roll with one divided portion of the cliché, the printing roll corresponding to the respective unit panel of the substrate, the whole circumferential circumference area of the printing roll corresponding to the area of one unit panel and the area of the divided portion of the cliché;

applying the resist transferred on the whole area of the surface of the blanket of the printing roll on the etching object layer on a one corresponding unit panel of the substrate; and

repeating the transferring process and applying process to the etching object layer on other unit panels of the substrate from other divided portions of the cliché using the printing roll.

2. (Previously Presented) The method of claim 1, wherein the printing roll has a same width as that of the corresponding unit panel of the substrate.

Claim 3 (Cancelled)

4. (Previously Presented) The method of claim 2, wherein a length of the blanket of the printing roll is the same as a length of a circumference of the printing roll, which is same as a length of the unit panel of the substrate.

Claims 5-6 (Cancelled)

7. (Previously Presented) The method of claim 1, wherein the printing roll is formed to have a same size as that of the unit panel the substrate.

8. (Original) The method of claim 1, wherein the etching object layer includes a metal layer.

9. (Original) The method of claim 1, wherein the etching object layer includes an insulating layer comprised of SiO<sub>x</sub> or SiN<sub>x</sub>.

10. (Original) The method of claim 1, wherein the etching object layer is a semiconductor layer.

Claims 11-27 (Cancelled)

28. (Previously Presented) The method of claim 1, wherein the blanket improves adhesive force with the resist.

Claims 29-34 (Cancelled)